

**AMENDMENTS TO THE CLAIMS**

**Please cancel claims 1-5 and 11-17 without prejudice or disclaimer and amend the claims as follows:**

1. (Canceled)

2. (Canceled)

3. (Canceled)

4. (Canceled)

5. (Canceled)

6. (Currently Amended) A light-emitting diode of a surface emitting type in which a semiconductor layer is deposited on a crystal growth plane of a crystal growth substrate, wherein

said crystal growth substrate comprises at least one of an output plane and a reflection plane which contributes to luminous output of the device through a physical shaping process ~~such as~~ including any of a polishing treatment, dicing treatment and blasting treatment, and

a physically damaged layer which is formed on the surface of at least one of said output plane and said reflection plane and remains owing to friction and shock generated in said shaping process is ~~removed~~. removed,

wherein the peak luminous wavelength of said light-emitting diode is less than 470nm.

7. (Original) A light-emitting diode according to claim 6, wherein a metal layer which has light-transparency to transmit light to the luminous extracting side of said device is formed on said output plane.

8. (Previously Presented) A light-emitting diode according to claim 6, wherein a metal layer which reflects light to the luminous extracting side of said device is formed on said reflection plane.

9. (Previously Presented) A light-emitting diode according to claim 6, wherein said crystal growth substrate is formed by using  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1$ ) or silicon carbide (SiC).

10. (Currently Amended) A light-emitting diode according to claim 6, wherein a taper plane which inclines to said crystal growth plane of said crystal growth substrate is formed at least as a portion of at least one of said output plane or at least as a portion of said reflection plane.

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Canceled)

16. (Canceled)

17. (Canceled)